

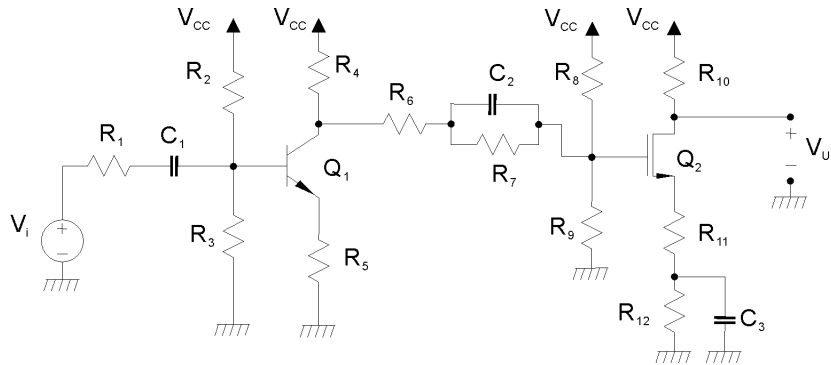
ELETTRONICA DIGITALE

Corso di Laurea in Ingegneria Informatica

Prova scritta del 17 febbraio 2014

Esercizio A

$R_1 = 50 \Omega$	$R_{10} = 1750 \Omega$
$R_3 = 270 \text{ k} \Omega$	$R_{11} = 100 \Omega$
$R_4 = 2 \text{ k} \Omega$	$R_{12} = 900 \Omega$
$R_5 = 1 \text{ k} \Omega$	$C_1 = 1 \text{ nF}$
$R_6 = 50 \Omega$	$C_2 = 3.3 \mu\text{F}$
$R_7 = 450 \Omega$	$C_3 = 200 \text{ nF}$
$R_8 = 9 \text{ k} \Omega$	$V_{CC} = 15 \text{ V}$
$R_9 = 2 \text{ k} \Omega$	



Q_1 è un transistor BJT BC109B resistivo con $h_{re} = h_{oe} = 0$. Q_2 è un transistor MOS a canale n resistivo, con la corrente di drain in saturazione data da $I_D = k(V_{GS} - V_T)^2$ con $k = 4 \text{ mA/V}^2$ e $V_T = 1 \text{ V}$.

Con riferimento al circuito in figura:

- 1) Calcolare il valore della resistenza R_2 in modo che, in condizioni di riposo, la tensione di uscita sia 8 V. Determinare, inoltre, il punto di riposo dei due transistori e verificare la saturazione di Q_2 . (R: $R_2 = 727959.18 \Omega$)
- 2) Determinare V_u/V_i alle frequenze per le quali C_1 , C_2 e C_3 possono essere considerati dei corto circuiti. (R: $V_u/V_i = 6.77$)
- 3) **(Solo per 12 CFU)** Determinare la funzione di trasferimento V_u/V_i e tracciarne il diagramma di Bode quotato asintotico del modulo. (R: $f_{z1} = 0 \text{ Hz}$; $f_{p1} = 1328 \text{ Hz}$; $f_{z2} = 107.18 \text{ Hz}$; $f_{p2} = 120.26 \text{ Hz}$; $f_{z3} = 884.2 \text{ Hz}$; $f_{p3} = 4421 \text{ Hz}$)

Esercizio B

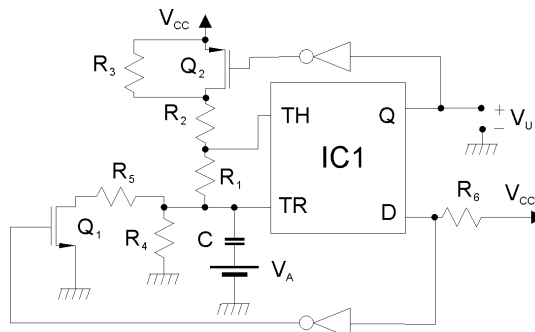
Progettare una porta logica in tecnologia CMOS, utilizzando la tecnica della pull-up network e della pull-down network, che implementi la funzione logica:

$$Y = (\overline{A + D})(\overline{B D + C} + \overline{E}) + (\overline{B + D})(\overline{A D + C}) + \overline{A C D} + \overline{A E}$$

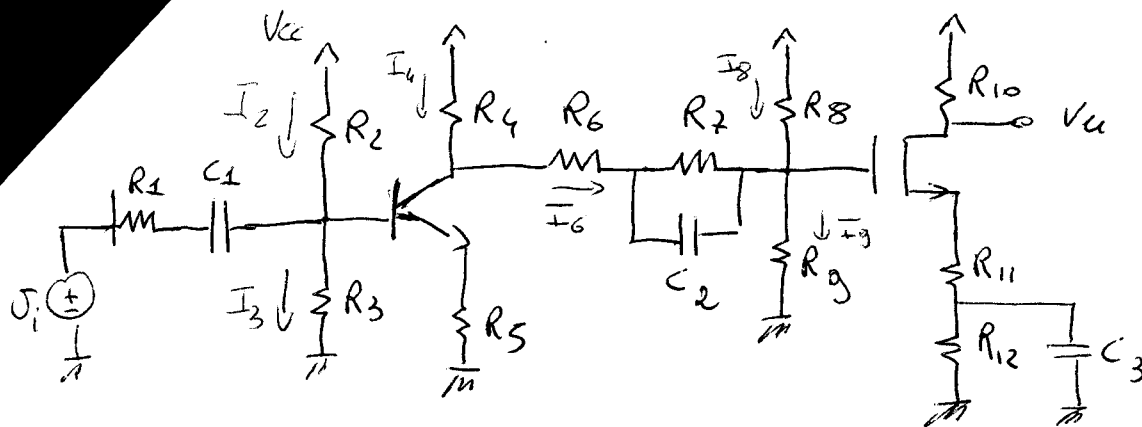
Determinare il numero dei transistori necessari e disegnarne lo schema completo. Dimensionare inoltre il rapporto (W/L) di tutti i transistori, assumendo, per l'inverter di base, W/L pari a 2 per il MOS a canale n e pari a 5 per quello a canale p. Si specifichino i dettagli della procedura di dimensionamento dei transistori.

Esercizio C

$R_1 = 200 \Omega$	$R_5 = 1 \text{ k} \Omega$
$R_2 = 800 \Omega$	$V_A = 0.5 \text{ V}$
$R_3 = 1 \text{ k} \Omega$	$C = 100 \text{ nF}$
$R_4 = 10 \text{ k} \Omega$	$V_{CC} = 5 \text{ V}$
$R_5 = 100 \Omega$	



Il circuito IC₁ è un NE555 alimentato a $V_{CC} = 5 \text{ V}$, Q_1 ha una $R_{on} = 0$ e $V_T = 1 \text{ V}$, Q_2 ha una $R_{on} = 0$ e $V_T = -1 \text{ V}$ e gli inverter sono ideali. Determinare la frequenza del segnale di uscita del multivibratore in figura. (R: $f = 17331 \text{ Hz}$)



R₃ = 270 kΩ

R₄ = 2 kΩ

R₅ = 1 kΩ

R₆ = 50 Ω

R₇ = 450 Ω

R₈ = 9 kΩ

R₉ = 2 kΩ

R₁₀ = 1750 Ω

R₁₁ = 100 Ω

R₁₂ = 900 Ω

V_{CC} = 15 V

$I_D = K(V_{GS} - V_T)^2$

$K = 4 \times 10^{-3} \text{ A/V}^2$

$V_T = 1 \text{ V}$

$g_m = 2K(V_{GS} - V_T) = 8 \times 10^{-3} \frac{\text{A}}{\text{V}}$

C₁ = 1 nF

C₂ = 3.3 μF

C₃ = 200 μF

1) Det. R₂ per V_u = 8 V

$$I_{10} = \frac{V_{CC} - V_u}{R_{10}} = \frac{15 - 8}{1750} = 4 \text{ mA} = I_D$$

$$V_S = I_{10}(R_{11} + R_{12}) = 4 \text{ V}$$

$$V_{DS} = 8 - 4 = 4 \text{ V}$$

$$V_{GS} = V_T + \sqrt{\frac{I_D}{K}} = 2 \text{ V} \quad \left. \begin{array}{l} V_{DS} > (V_{GS} - V_T) \\ 4 > 1 \end{array} \right\}$$

$$V_G = V_{GS} + V_S = 6 \text{ V}$$

$$I_9 = \frac{V_G}{R_9} = 3 \text{ mA}$$

$$I_8 = \frac{V_{CC} - V_G}{R_8} = 1 \text{ mA}$$

$$I_6 = I_9 - I_8 = 2 \text{ mA}$$

$$V_C = V_G + R_{67}(R_6 + R_7)I_6 = 7 \text{ V}$$

$$I_4 = \frac{V_{CC} - V_C}{R_4} = 4 \text{ mA}$$

$$I_C = I_4 - I_6 = 2 \text{ mA}$$

$$I_C \approx I_E$$

$$V_E = I_E R_5 = 2 \text{ V}$$

$$V_{CE} = V_C - V_E = 5 \text{ V}$$

$$V_B = V_E + V_G = 2.2 \text{ V}$$

$$I_3 = \frac{V_B}{R_3} = 10 \mu\text{A}$$

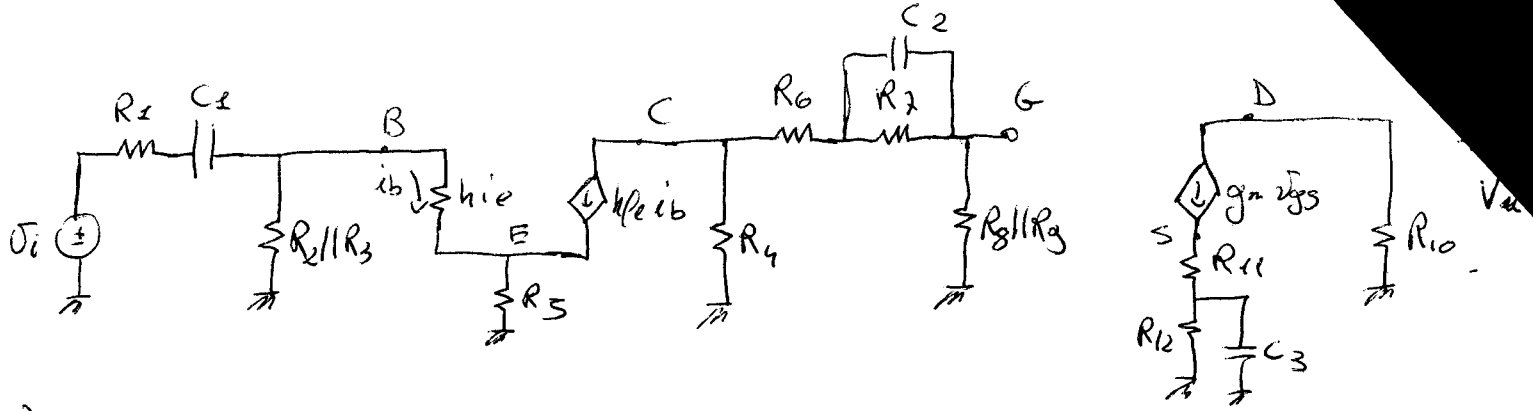
$$I_2 = I_3 + I_B = 16.8965 \mu\text{A}$$

$$R_2 = \frac{V_{CC} - V_B}{I_2} = 727959.18 \Omega$$

$$I_B = \frac{I_C}{h_{FE}} = 6.8965 \mu\text{A}$$

$$h_{FE} = 230$$

$$h_{FE} = 300$$



1) A_{CB}

$$V_u = -(g_m V_{gs}) R_{10}$$

$$V_s = (g_m V_{gs}) R_{11}$$

$$V_{gs} = V_g - g_m V_{gs} R_{11} = \frac{V_g}{1 + g_m R_{11}}$$

$$V_g = -(R_8 || R_9) \left[(h_{fe} i_b) \frac{R_4}{R_4 + R_6 + R_8 || R_9} \right]$$

$$i_b = V_i \frac{R_2 || R_3}{R_1 + R_2 || R_3} \frac{1}{(R_1 || R_2 || R_3) + h_{ie} + R_5 (h_{fe} + 1)}$$

$$A_{CB} = \frac{V_u}{V_i} = \frac{g_m R_{10}}{1 + g_m R_{11}} (R_8 || R_9) \frac{h_{fe} R_4}{R_4 + R_6 + R_8 || R_9} \frac{R_2 || R_3}{R_1 + R_2 || R_3} \frac{1}{(R_1 || R_2 || R_3) + h_{ie} + R_5 (h_{fe} + 1)}$$

$$= 6.771 \quad (16.61 \text{ dB})$$

CONDENSATORE C_1

$$1) f_{z1} = \phi$$

$$R_{VC1} = R_1 + R_2 || R_3 || [h_{ie} + R_5 (h_{fe} + 1)] = 119846.08 \Omega$$

$$1) f_{p1} = \frac{1}{2\pi C_1 R_{VC1}} = 1327.33 \text{ Hz}$$

CONDENSATORE C_2

$$1) f_{z2} = \frac{1}{2\pi C_2 R_7} = 107.175 \text{ Hz}$$

$$R_{VC2} = R_7 || [R_6 + R_4 + R_8 || R_9] = 401.04 \Omega$$

$$f_{p2} = \frac{1}{2\pi C_2 R_{VC2}} = 120.259 \text{ Hz}$$

SATORE C_3

$$f_{23} = \frac{1}{2\pi C_3 R_{12}} = 884.19 \text{ Hz}$$

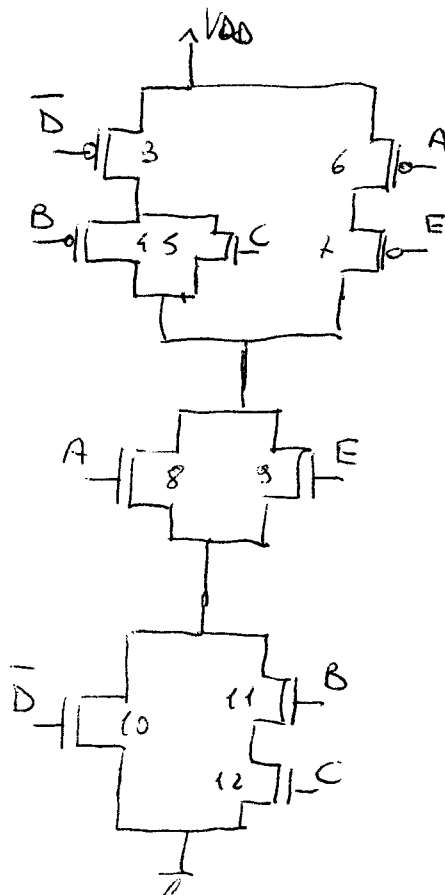
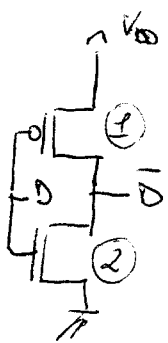
$$R_{Vc3} = R_{12} \parallel \left[\frac{1}{g_m} + R_{11} \right] = 180 \Omega$$

$$f_{p3} = \frac{1}{2\pi C_3 R_{Vc3}} = 4420.92 \text{ Hz}$$

ESERCIZIO B

$$\begin{aligned} Y &= (\overline{A+B})(\overline{B+D}) + (\overline{B+D})(\overline{A+C}) + \overline{A} \overline{C} D + \overline{A} \overline{E} = \\ &= (\overline{A} \overline{B})(\overline{B} \overline{D} + \overline{C} + \overline{E}) + (\overline{B} \overline{D})(\overline{A} \overline{C} + \overline{E}) + \overline{A} \overline{C} D + \overline{A} \overline{E} = \\ &= \overline{A} \overline{B} \overline{D} + \overline{A} \overline{B} \overline{D} \overline{C} + \overline{A} \overline{B} \overline{D} \overline{E} + \overline{A} \overline{B} \overline{D} \overline{C} \overline{E} + \overline{B} \overline{D} \overline{A} \overline{C} + \overline{B} \overline{D} \overline{A} \overline{E} + \overline{A} \overline{C} D + \overline{A} \overline{E} = \\ &= \overline{B} \overline{D} + \overline{C} \overline{D} + \overline{A} \overline{E} = \\ &= D(\overline{B} + \overline{C}) + \overline{A} \overline{E} \end{aligned}$$

12 MOSFET



$Q_1: P \quad Q_2: n$

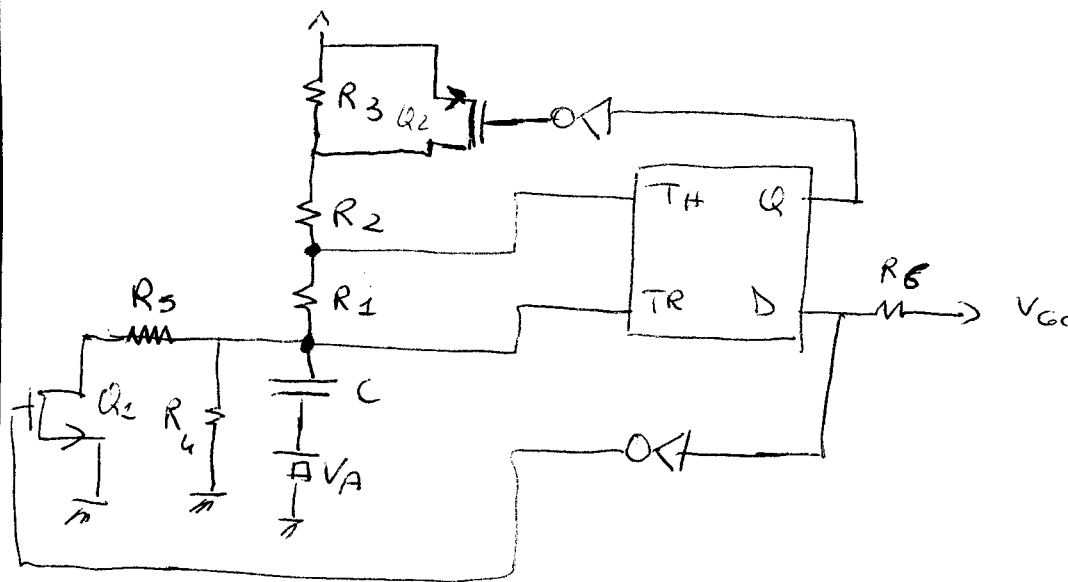
PUN: $Q_3, Q_4, Q_5, Q_6, Q_7: 2p$

PDN

$Q_8, Q_9, Q_{11}, Q_{12}: 3n$

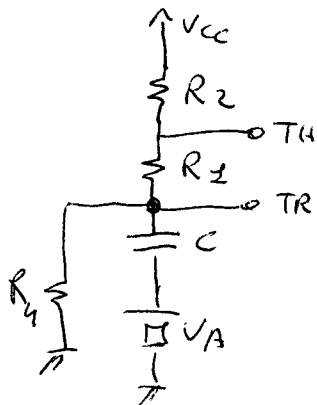
$$\frac{1}{x_{10}} + \frac{1}{3n} = \frac{1}{n}$$

$$\frac{1}{x_{10}} = \frac{2}{3n} \Rightarrow Q_{10} = \frac{3}{2}n = 1.5n$$



$R_1 = 200 \Omega$
 $R_2 = 800 \Omega$
 $R_3 = 100 \Omega$
 $R_4 = 10 \text{ k}\Omega$
 $V_A = 0.5 \text{ V}$
 $C = 100 \text{ nF}$
 $R_5 = 300 \Omega$

- 1) $Q_1 = 1$ $\Rightarrow V_{gs1} = 0 \text{ V}$ $V_{ds1} = 5 \text{ V} \Rightarrow V_{gs1} = -5 < V_T \Rightarrow Q_1 \text{ ON}$
 $D = \text{H.T.}$ $Q_2 \text{ OFF}$



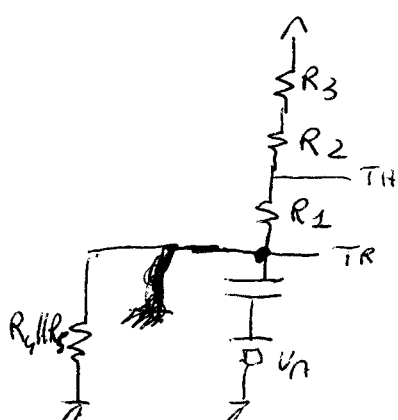
$V_{GS1} = \frac{1}{3} V_{CC} - V_A = 1.16 \text{ V}$
 $V_{GS1} = V_{CC} \frac{R_4}{R_4 + R_1 + R_2} - V_A = 4.045 \text{ V}$
 $I_{R1} = \left(V_{CC} - \frac{2}{3} V_{CC} \right) \frac{1}{R_2} = 2.083 \text{ mA}$
 $V_{TR} = \frac{2}{3} V_{CC} - R_1 I_{R1} = 2.916 \text{ V}$
 $V_{CCOR} = V_{TR} - V_A = 2.416 \text{ V}$

$R_{V_{GS1}} = R_4 \parallel (R_1 + R_2) = 909.09 \Omega$

$\tau_1 = C R_{V_{GS1}} = 9.09 \times 10^{-5} \text{ s}$

$T = \tau_1 \ln \frac{V_{GS1} - V_{GS1}}{V_{CCOR} - V_{GS1}} = 5.177 \times 10^{-5} \text{ s}$

- 2) $Q_1 = 0 \Rightarrow Q_2 \text{ OFF}$
 $D = 0 \Rightarrow Q_1 \text{ ON}$



$V_{GS2} = 2.416 \text{ V}$
 $V_{GS2} = 1.16 \text{ V}$
 $V_{GS2} = V_{CC} \frac{R_4 \parallel R_5}{(R_4 \parallel R_5) + R_1 + R_2 + R_3} - V_A = -0.264 \text{ V}$

$V_i < V_{CCOR} < V_f$
 $1.16 \text{ V} < 2.416 \text{ V} < 4.045 \text{ V}$

$V_i > V_{CCOR} > V_f$
 $2.416 \text{ V} > 1.16 \text{ V} > -0.264 \text{ V}$

$$R_4 || R_5 || (R_1 + R_2 + R_3) = 94.34 \Omega$$

$$\tau_2 = 9.434 \mu s$$

$$T_2 = 5.9238 \mu s$$

$$T = T_1 + T_2 = 5.77 \times 10^{-5} s$$

$$f = \underline{\underline{17331.145 \text{ Hz}}}$$